

August 28 (Wed.)

Session	Start time	Allotted time(min)	No.	Title	Speaker	Affiliation	Type
7. Power 2 Yoshitsugu Yamamoto Martin Kuball	8:30	25	7-1	High Performance Vertical GaN-on-GaN pn Power Diodes	Wu Lu	Ohio State Univ., USA	invited
	8:55	25	7-2	Die-Level Functional Off-Chip Characterization of Power Devices Using Optical Techniques	Xavier Perpinya	IMB-CNM, Spain	invited
	9:20	15	7-3	High performance fully vertical GaN on Silicon PIN diodes for next generation power devices	Youssef Hamdaoui	CNRS-IEMN, France/Siltronic AG, Germany/Ghent Univ., Belgium	upgrade
	9:35	3	7-4	Fabrication of vertical GaN junction barrier Schottky diodes using Mg ion implantation	Kazuki Kitagawa	Nagoya Univ./Toyota Central R&D Labs. Inc., Japan	sp
Coffee Break	9:40-10:00						
8. GaN Thermal Management, Process Masataka Higashiwaki Xavier Perpinya	10:00	25	8-1	Considerations for the Thermal Design of Ultrawide Bandgap Semiconductor Devices	Samuel Graham	Univ. of Maryland/Univ. of Virginia /Univ. of South Carolina/UCLA /Georgia Tech/Naval Research Lab./Univ. of Notre Dame, USA	invited
	10:25	25	8-2	Heterogenous diamond-GaN integration for device-level thermal management	Mohamadali Malakoutian	Stanford Univ., USA	invited
	10:50	3	8-3	P-type Ohmic Contact with Annealed Mg Process	Min-Jeoung Kim	Hongik Univ./ChipsK Corp., South Korea	sp
	10:53	3	8-4	Fabrication of Recessed-gate AlGaIn/GaN HEMTs utilizing Contactless Photoelectrochemical (CL-PEC) Etching	Naoki Shiozawa	Hokkaido Univ., Japan	sp
	10:56	3	8-5	Photo-electrochemical (PEC) etching and characterization of the damaged GaN surface	Takahiro Shimazaki	Hokkaido Univ., Japan	sp
	10:59	3	8-6	Multi-probe Hall measurements for Ohmic contacts to thin-AlGaIn/GaN heterostructures with no two-dimensional electron gas	Kazuya Uryu	Advantest Laboratories Ltd. /JAIST/Mitsubishi Electric Corp., Japan	sp
	11:02	3	8-7	Novel on-wafer Hall measurement method with ohmic formation using high voltage pulses	K. Kodama	NYCU, Taiwan/Yamamotogiken /Seiken, Japan	sp
	11:05	3	8-8	Simulation study on GaN-based npn HBTs with MQW structured p-base region	Ryosei Inoue	Nagoya Inst. of Tech., Japan	sp
Excursion	11:30-						
Banquet	19:00-21:00						